

WHAT IS CLAIMED IS:

1 1. A die with text deposited upon the die using semiconductor processing
2 techniques, the die comprising:

3 a substrate which is cut from a wafer comprising a plurality of substrates;

4 a first paragraph in contact with the substrate; and

5 a second paragraph in contact with the substrate and aligned with the first
6 paragraph in a column.

1 2. The die with text deposited upon the die using semiconductor
2 processing techniques of claim 1, wherein:

3 the substrate is a semiconductor substrate; and

4 text in the column is comprised of one or more of a metal, an oxide, a
5 polysemiconductor and a photoresist.

1 3. The die with text deposited upon the die using semiconductor
2 processing techniques of claim 1, wherein the first and second paragraphs are comprised of a
3 plurality of characters.

1 4. The die with text deposited upon the die using semiconductor
2 processing techniques of claim 3, wherein each of the plurality of characters is comprised of a
3 plurality of primitives.

1 5. The die with text deposited upon the die using semiconductor
2 processing techniques of claim 1, the die further comprising:

3 a first character appearing in a first color; and

4 a second character appearing in a second color.

1 6. The die with text deposited upon the die using semiconductor
2 processing techniques of claim 1, the die further comprising an image on the substrate.

1 7. A method for depositing a plurality of paragraphs of text on a substrate
2 with semiconductor processing techniques, the method comprising:

3 reading a first paragraph from an electronic source;
4 reading a second paragraph from the electronic source;
5 positioning the first and second paragraphs into a column;
6 generating an electronic file at least partially representative of the column; and
7 imaging the substrate with the column, wherein the substrate is cut from a
8 wafer having a plurality of substrates.

1 8. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, wherein the
3 imaging the substrate includes lithographing the substrate with a mask.

1 9. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, the method further
3 comprising:

4 converting a first character of the first paragraph into a first pattern;
5 converting a second character of the first paragraph into a second pattern; and
6 aligning the first and second characters on a line.

1 10. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, wherein the
3 substrate is a semiconductor wafer.

1 11. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, the method further
3 comprising determining an end of a first line in the first paragraph and beginning a second
4 line.

1 12. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, the method further
3 comprising determining an end of the first paragraph and beginning the second paragraph on
4 the next line of the column.

1 13. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, the method further
3 comprising detecting an end of a first column and depositing a next line in a second column.

1 14. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, the method further
3 comprising:

4 determining a first color for a first character; and

5 determining a second color for a second character.

1 15. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 7, wherein the
3 generating the electronic file comprises overlaying a silhouette over at least part of the
4 column.

1 16. A lithographing system for depositing a plurality of paragraphs on a
2 substrate, the lithographing system comprising:

3 a radiation source;

4 the substrate; and

5 a mask generated from an electronic file, wherein:

6 the mask is between the radiation source and the substrate, and

7 the mask includes a first and second paragraphs arranged in a column.

1 17. The lithographing system for depositing the plurality of paragraphs on
2 the substrate as recited in claim 16, wherein the electronic file comprises a plurality of
3 elements corresponding to characters for the plurality of paragraphs.

1 18. The lithographing system for depositing the plurality of paragraphs on
2 the substrate as recited in claim 17, wherein each character of the first and second paragraphs
3 is comprised of a plurality of rectangles wherein one side of the rectangle is equal in size to
4 the process resolution.

1 19. The lithographing system for depositing the plurality of paragraphs on
2 the substrate as recited in claim 16, wherein the first and second paragraphs are separated by
3 at least one of: a hard return, a tab and an enlarged character.

1 20. The lithographing system for depositing the plurality of paragraphs on
2 the substrate as recited in claim 16, the lithographing system further comprising:

3 a first character visible as a first color; and

4 a second character visible as a second color.

1 21. A method for depositing text and an image on a substrate with
2 semiconductor processing techniques, the method comprising:

3 loading a phrase;

4 loading a silhouette image;

5 providing a mask file at least partially representative of the phrase and the
6 silhouette image, wherein the generating step comprises overlaying a silhouette over at least
7 part of the phrase; and

8 imaging the substrate with the electronic file.

1 22. The method for depositing text and the image on the substrate with
2 semiconductor processing techniques as recited in claim 21, wherein the imaging the
3 substrate includes lithographing the substrate with a mask.

1 23. The method for depositing text and the image on the substrate with
2 semiconductor processing techniques as recited in claim 21, the method further comprising:

3 converting a first character of the phrase into a first pattern;

4 converting a second character of the phrase into a second pattern; and

5 aligning the first and second characters on a line.

1 24. The method for depositing text and the image on the substrate with
2 semiconductor processing techniques as recited in claim 21, wherein the substrate is a
3 semiconductor wafer.

1 25. The method for depositing text and the image on the substrate with
2 semiconductor processing techniques as recited in claim 21, the method further comprising:
3 determining a first color for a first character; and
4 determining a second color for a second character.

1 26. A method for depositing a plurality of paragraphs of text on a substrate
2 with semiconductor processing techniques, the method comprising:
3 reading a first paragraph from an electronic source;
4 reading a second paragraph from the electronic source;
5 positioning the first and second paragraphs into one or more columns;
6 generating an electronic file at least partially representative of the column; and
7 producing the column on the substrate using semiconductor processing
8 techniques, wherein the substrate is cut from a wafer having a plurality of substrates.

1 27. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, wherein the
3 producing step includes lithographing the substrate with a mask.

1 28. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, the method further
3 comprising:
4 converting a first character of the first paragraph into a first pattern;
5 converting a second character of the first paragraph into a second pattern; and
6 aligning the first and second characters on a line.

1 29. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, wherein the
3 substrate is a semiconductor wafer.

1 30. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, the method further

3 comprising determining an end of a first line in the first paragraph and beginning a second
4 line.

1 31. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, the method further
3 comprising determining an end of the first paragraph and beginning the second paragraph on
4 the next line of the column.

1 32. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, the method further
3 comprising detecting an end of a first column and depositing a next line in a second column.

1 33. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, the method further
3 comprising:

4 determining a first color for a first character; and
5 determining a second color for a second character.

1 34. The method for depositing the plurality of paragraphs of text on the
2 substrate with semiconductor processing techniques as recited in claim 26, wherein the
3 generating the electronic file comprises overlaying a silhouette over at least part of the
4 column.